

HIGH SPEED 2K x 8 DUAL PORT STATIC RAM

IDT7132SA/LA IDT7142SA/LA

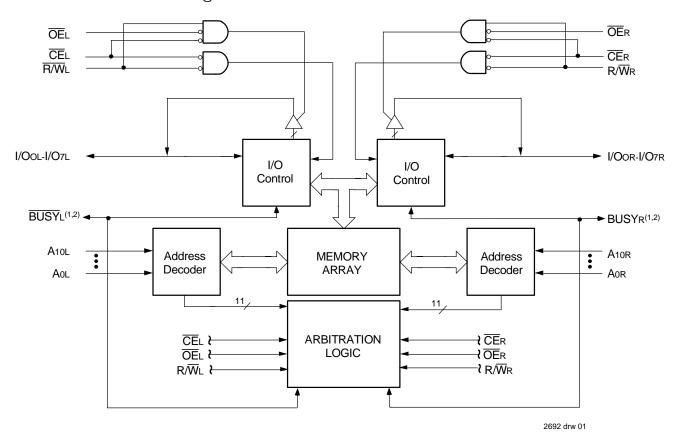
LEAD FINISH (SnPb) ARE IN EOL PROCESS - LAST TIME BUY EXPIRES JUNE 15, 2018

Features

- High-speed access
 - Commercial: 20/25/35/55/100ns (max.)
 - Industrial: 25ns (max.)
 - Military: 25/35/55/100ns (max.)
- Low-power operation
 - IDT7132/42SA
 - Active: 325mW (typ.)
 - Standby: 5mW (typ.)
 - IDT7132/42LA
 - Active: 325mW (typ.) Standby: 1mW (typ.)

- MASTER IDT7132 easily expands data bus width to 16-or-more bits using SLAVE IDT7142
- ◆ On-chip port arbitration logic (IDT7132 only)
- ◆ BUSY output flag on IDT7132; BUSY input on IDT7142
- ◆ Battery backup operation —2V data retention (LA only)
- ◆ TTL-compatible, single 5V ±10% power supply
- Available in 48-pin DIP, LCC and Flatpack, and 52-pin PLCC packages
- Military product compliant to MIL-PRF-38535 QML
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information

Functional Block Diagram



NOTES:

- IDT7132 (MASTER): BUSY is open drain output and requires pullup resistor of 270Ω.
 IDT7142 (SLAVE): BUSY is input.
- 2. Open drain output: requires pullup resistor of 270Ω .

JULY 2018

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Description

The IDT7132/IDT7142 are high-speed 2K x 8 Dual-Port Static RAMs. The IDT7132 is designed to be used as a stand-alone 8-bit Dual-Port RAM or as a "MASTER" Dual-Port RAM together with the IDT7142 "SLAVE" Dual-Port in 16-bit-or-more word width systems. Using the IDT MASTER/ SLAVE Dual-Port RAM approach in 16-or-more-bit memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

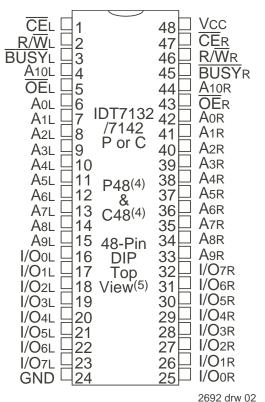
Both devices provide two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by \overline{CE} permits the on-chip circuitry of each port to enter

a very low standby power mode.

Fabricated using CMOS high-performance technology, these devices typically operate on only 325mW of power. Low-power (LA) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

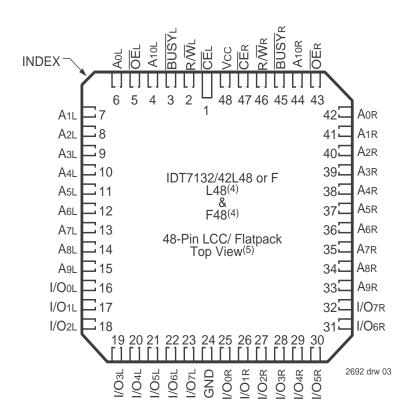
The IDT7132/7142 devices are packaged in a 48-pin sidebraze or plastic DIPs, 48-pin LCCs, 52-pin PLCCs, and 48-lead flatpacks. Military grade product is manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

Pin Configurations^(1,2,3)



OTES:

- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- P48-1 package body is approximately .55 in x 2.43 in x .18 in. C48-2 package body is approximately .62 in x 2.43 in x .15 in. L48-1 package body is approximately .57 in x .57 in x .68 in. F48-1 package body is approximately .75 in x .75 in x .11 in.
- This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.



Capacitance⁽¹⁾ (TA = +25°C,f = 1.0MHz)

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	11	pF
Соит	Output Capacitance	Vout = 3dV	11	pF

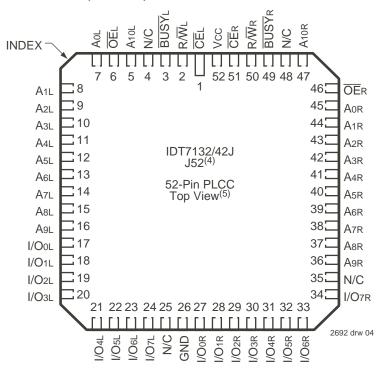
NOTES:

 This parameter is determined by device characterization but is not production tested.

2692 tbl 00

3dV represents the interpolated capacitance when the input and output signals switch from 3V to 0V.

Pin Configurations^(1,2,3) (con't.)



NOTES:

- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- 3. Package body is approximately .75 in x .75 in x .17 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Absolute Maximum Ratings(1)

Absolute Maximam Ratings									
Symbol	Rating	Commercial & Industrial	Military	Unit					
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V					
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C					
TSTG	Storage Temperature	-65 to +150	-65 to +150	°C					
lout	DC Output Current	50	50	mA					

NOTES:

Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may
cause permanent damage to the device. This is a stress rating only and functional
operation of the device at these or any other conditions above those indicated in
the operational sections of the specification is not implied. Exposure to absolute
maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

Recommended Operating Temperature and Supply Voltage^(1,2)

Grade	Ambient Temperature	GND	Vcc
Military	-55°C to+125°C	0V	5.0V <u>+</u> 10%
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

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NOTES:

- 1. This is the parameter Ta. This is the "instant on" case temperature.
- Industrial temperature: for specific speeds, packages and powers contact your sales office.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
V⊪	Input High Voltage	2.2		6.0(2)	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.8	V

2692 tbl 03

NOTES:

- V_I (min.) = -1.5V for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 10%.

2692 tbl 01

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(1,5,8)}$ (Vcc = 5.0V ± 10%)

					(/			
					7142	X20 ⁽²⁾ X20 ⁽²⁾ I Only	7142 Com	X25 ⁽⁷⁾ X25 ⁽⁷⁾ 'I, Ind ilitary	714: Con	2X35 2X35 n'l & itary	
Symbol	Parameter	Test Condition	Vers	ion	Тур.	Max.	Тур.	Max.	Тур.	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	CEL = CER = VIL, Outputs Disabled f = fMAX ⁽³⁾	COM'L	SA LA	110 110	250 200	110 110	220 170	80 80	165 120	mA
		I = IMAX ^e /	MIL & IND	SA LA			110 110	280 220	80 80	230 170	
ISB1	Standby Current (Both Ports - TTL $f = \overline{CE}R = VIH$, Level Inputs)	COM'L	SA LA	30 30	65 45	30 30	65 45	25 25	65 45	mA	
	Level inpuis)	5)	MIL & IND	SA LA	_		30 30	80 60	25 25	80 60	
ISB2	Standby Current (One Port - TTL	CE"A" = VIL and CE"B" = VIH ⁽⁶⁾ Active Port Outputs Disabled	COM'L	SA LA	65 65	165 125	65 65	150 115	50 50	125 90	mA
	Level Inputs) f=fMAX ⁽³⁾	MIL & IND	SA LA			65 65	160 125	50 50	150 115		
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	$\overline{\text{CE}}\text{L}$ and $\overline{\text{CE}}\text{R} \geq \text{VCC -0.2V}$ VIN $\geq \text{VCC -0.2V}$ or VIN $\leq 0.2\text{V}$, f = 0 ⁽⁴⁾	COM'L	SA LA	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 4	mA
	Civios Level Inpuis)	Inputs)	MIL & IND	SA LA			1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	(One Port - All VIN > VCC - 0.2V or VIN < 0.2V	VIN > VCC - 0.2V or VIN < 0.2V	COM'L	SA LA	60 60	155 115	60 60	145 105	45 45	110 85	mA
	CMOS Level Inputs)	Active Port Outputs Disabled f = fMAX ⁽³⁾	MIL & IND	SA LA	_		60 60	155 115	45 45	145 105	

2692 tbl 04a

2692 tbl 04b

					7132X55 7142X55 Com'l & Military		7132X100 7142X100 Com'l & Military		
Symbol	Parameter	Test Condition	Versi	on	Тур.	Max.	Тур.	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	CEL = CER = VIL, Outputs Disabled f = fmax ⁽³⁾	COM'L	SA LA	65 65	155 110	65 65	155 110	mA
	(Buil Fulls Active)	I = IWAX'	MIL & IND	SA LA	65 65	190 140	65 65	190 140	
ISB1	Standby Current (Both Ports - TTL Level Inputs) $ \overline{\textbf{CEL}} = \overline{\textbf{CER}} = \textbf{VIH}, \\ f = f\text{MAX}^{(S)} $	COM'L	SA LA	20 20	65 35	20 20	55 35	mA	
	Level inpuis)		MIL & IND	SA LA	20 20	65 45	20 20	65 45	
ISB2	Standby Current \overline{CE} 'A" = VIL and \overline{CE} 'B" = VIH $^{(6)}$ Active Port Outputs Disabled	COM'L	SA LA	40 40	110 75	40 40	110 75	mA	
	Level Inputs)	f=fMAX ⁽³⁾	MIL & IND	SA LA	40 40	125 90	40 40	125 90	
ISB3	Full Standby Current (Both Ports - All	$\overline{CE}L$ and $\overline{CE}R \ge VCC -0.2V$ $VIN \ge VCC -0.2V$ or $VIN \le 0.2V$, $f = 0^{(4)}$	COM'L	SA LA	1.0 0.2	15 4	1.0 0.2	15 4	mA
	CMOS Level Inputs)		MIL & IND	SA LA	1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - All	One Port - All $VIN \ge \overline{VCC} - 0.2V$ or $VIN \le 0.2V$	COM'L	SA LA	40 40	100 70	40 40	95 70	mA
	CMOS Level Inputs)	Active Port Outputs Disabled $f = f_{MAX}^{(3)}$	MIL & IND	SA LA	40 40	110 85	40 40	110 80	

- 1. 'X' in part numbers indicates power rating (SA or LA).
- 2. PLCC Package only
- 3. At f = fMax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC TEST CONDITIONS" of input levels
- 4. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
- 5. Vcc = 5V, Ta=+25°C for Typ and is not production tested. Vcc pc = 100mA (Typ)
- 6. Port "A" may be either left or right port. Port "B" is opposite from port "A".
- Not available in DIP packages.
- Industrial temperature: for specific speeds, packages and powers contact your sales office.

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range (Vcc = 5.0V ± 10%)

			7132SA 7142SA		713 714		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
Iu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, Vin = 0V to Vcc		10		5	μΑ
ILO	Output Leakage Current	$\frac{\text{Vcc}}{\text{CE}} = 5.5\text{V},$ $\frac{\text{CE}}{\text{CE}} = \text{ViH}, \text{Vout} = 0\text{V to Vcc}$		10	1	5	μΑ
Vol	Output Low Voltage	IoL = 4mA		0.4	-	0.4	V
Vol	Open Drain O <u>utput</u> Low Voltage (BUSY)	IoL = 16mA		0.5	1	0.5	٧
Vон	Output High Voltage	IOH = -4mA	2.4	_	2.4	_	٧

2692 tbl 05

2692 tbl 06

NOTE:

1. At $Vcc \le 2.0V$ leakages are undefined.

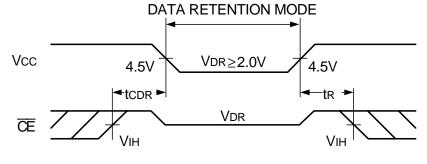
Data Retention Characteristics (LA Version Only)

Symbol	Parameter	Test Condition	Min.	Typ. ⁽¹⁾	Max.	Unit	
VDR	Vcc for Data Retention	Vcc = 2.0V		2.0	_		V
ICCDR	Data Retention Current	CE ≥ Vcc -0.2V	Mil. & Ind.	_	100	4000	μΑ
		VIN > Vcc -0.2V or	Com'l.	_	100	1500	μΑ
tcdr ⁽³⁾	Chip Deselect to Data Retention Time	VIN <u>≤</u> 0.2V		0	_		ns
tR ⁽³⁾	Operation Recovery Time			trc ⁽²⁾	_	_	ns

NOTES:

- 1. Vcc = 2V, Ta = +25°C, and is not production tested.
- 2. trc = Read Cycle Time
- 3. This parameter is guaranteed but not production tested.

Data Retention Waveform



2692 drw 05

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

2692 tbl 07

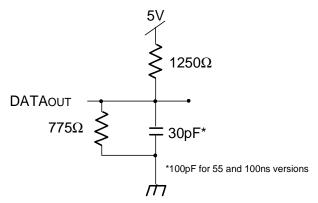


Figure 1. AC Output Test Load

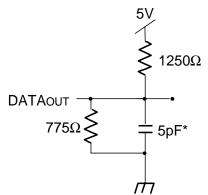


Figure 2. Output Test Load (for thz, tLz, twz, and tow)

* Including scope and jig

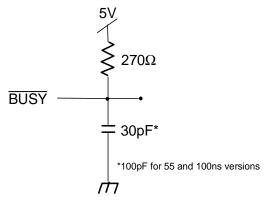


Figure 3. BUSY AC Output Test Load

2692 drw 06

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(3,5)

		7132X20 ⁽²⁾ 7142X20 ⁽²⁾ Com'l Only		7142 Com	7132X25 ⁽²⁾ 7132X35 7142X25 ⁽²⁾ 7142X35 Com'l, Ind Com'l & & Military Military					
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit		
READ CYCLE										
trc	Read Cycle Time	20		25	_	35		ns		
taa	Address Access Time		20	-	25		35	ns		
tace	Chip Enable Access Time		20		25		35	ns		
taoe	Output Enable Access Time		11		12		20	ns		
tон	Output Hold from Address Change	3		3		3		ns		
tLz	Output Low-Z Time ^(1,4)	0		0		0		ns		
tHZ	Output High-Z Time ^(1,4)		10		10		15	ns		
tpu	Chip Enable to Power Up Time ⁽⁴⁾	0	_	0	_	0	_	ns		
tpD	Chip Disable to Power Down Time ⁽⁴⁾		20	_	25	_	35	ns		

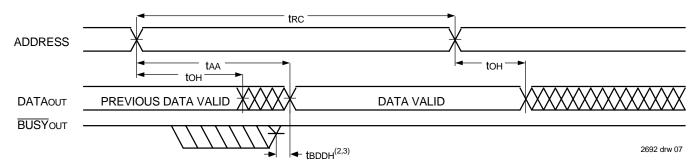
2692 tbl 08a

		7132X55 7142X55 Com'l & Military		7132X100 7142X100 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYC	CLE					
trc	Read Cycle Time	55	_	100	_	ns
taa	Address Access Time	_	55	_	100	ns
tace	Chip Enable Access Time		55	1	100	ns
taoe	Output Enable Access Time		25		40	ns
tон	Output Hold from Address Change	3	_	10		ns
tLZ	Output Low-Z Time ^(1,4)	5	_	5		ns
tHZ	Output High-Z Time ^(1,4)		25		40	ns
tpu	Chip Enable to Power Up Time (4)	0	_	0		ns
tPD	Chip Disable to Power Down Time ⁽⁴⁾		50		50	ns

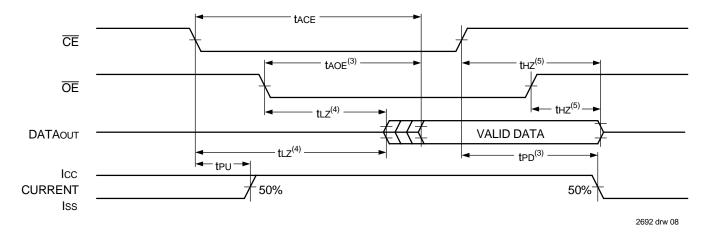
2692 tbl 08b

- 1. Transition is measured 0mV from Low or High-Impedance Voltage Output Test Load (Figure 2).
- 2. PLCC package only.
- 3. 'X' in part numbers indicates power rating (SA or LA).
- 4. This parameter is guaranteed by device characterization, but is not production tested.5. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Timing Waveform of Read Cycle No. 1, Either Side⁽¹⁾



Timing Waveform of Read Cycle No. 2, Either Side⁽¹⁾



- 1. $R/\overline{W} = VIH, \overline{CE} = VIL,$ and is $\overline{OE} = VIL.$ Address is valid prior to the coincidental with \overline{CE} transition LOW.
- 2. tbbb delay is required only in the case where the opposite port is completing a write operation to the same address location. For simultaneous read operations, BUSY has no relationship to valid output data.
- 3. Start of valid data depends on which timing becomes effective last taoe, tace, taa, and tbdd.
- 4. Timing depends on which signal is asserted last, $\overline{\sf OE}$ or $\overline{\sf CE}$.
- 5. Timing depends on which signal is de-asserted first, $\overline{\sf OE}$ or $\overline{\sf CE}$.

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range^(5,6)

•		7132 7142	X20 ⁽²⁾ X20 ⁽²⁾ I Only	7132X25 ⁽²⁾ 7142X25 ⁽²⁾ Com'l, Ind & Military		7132X35 7142X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE								
twc	Write Cycle Time ⁽³⁾	20	_	25	_	35	_	ns
tew	Chip Enable to End-of-Write	15	_	20	_	30	_	ns
taw	Address Valid to End-of-Write	15		20		30		ns
tas	Address Set-up Time	0		0		0		ns
twp	Write Pulse Width ⁽⁴⁾	15	_	15	_	25	_	ns
twr	Write Recovery Time	0		0		0		ns
tow	Data Valid to End-of-Write	10		12		15		ns
tHZ	Output High-Z Time ⁽¹⁾	_	10		10		15	ns
tон	Data Hold Time	0	_	0	_	0		ns
twz	Write Enable to Output in High- $\mathbb{Z}^{(1)}$	_	10		10	_	15	ns
tow	Output Active from End-of-Write ⁽¹⁾	0	_	0	_	0	_	ns

2692 tbl 09

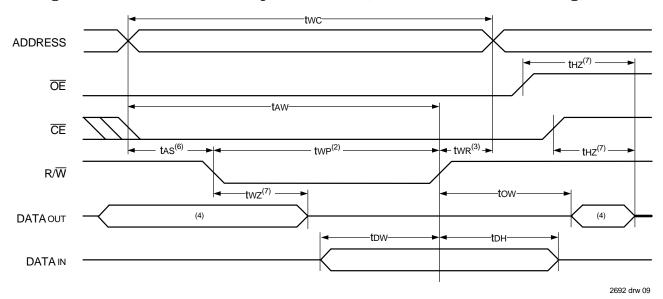
		7142 Con	2X55 2X55 n'l & tary	7132X100 7142X100 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
WRITE CYCLI	Ē					
twc	Write Cycle Time ⁽³⁾	55		100	_	ns
tew	Chip Enable to End-of-Write	40		90	_	ns
taw	Address Valid to End-of-Write	40	-	90		ns
tas	Address Set-up Time	0	-	0	_	ns
twp	Write Pulse Width ⁽⁴⁾	30	-	55	_	ns
twr	Write Recovery Time	0	-	0		ns
tow	Data Valid to End-of-Write	20	-	40		ns
tHZ	Output High-Z Time ⁽¹⁾	-	25		40	ns
tDH	Data Hold Time	0	-	0	_	ns
twz	Write Enable to Output in High-Z ⁽¹⁾	-	30		40	ns
tow	Output Active from End-of-Write ⁽¹⁾	0	_	0	_	ns

NOTES:

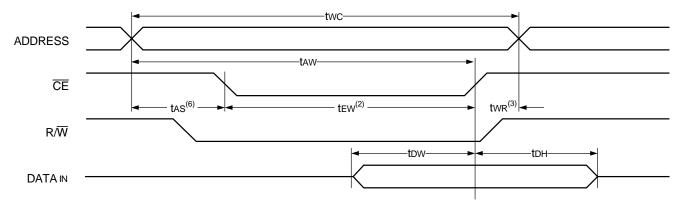
- 1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2). This parameter is guaranteed by device characterization but is not production tested.
- 2. PLCC package only.
- 3. For Master/Slave combination, two = tbaa + twp, since R/W = VIL must occur after tbaa.
- 4. If \overline{OE} is LOW during a R/ \overline{W} controlled write cycle, the write pulse width must be the larger of twp or (twz + tbw) to allow the I/O drivers to turn off data to be placed on the bus for the required tbw. If \overline{OE} is High during a R/ \overline{W} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 5. 'X' in part numbers indicates power rating (SA or LA).
- 6. Industrial temperature: for specific speeds, packages and powers contact your sales office.

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Timing Waveform of Write Cycle No. 1, (R/W Controlled Timing)(1,5,8)



Timing Waveform of Write Cycle No. 2, (CE Controlled Timing)(1,5)



NOTES:

2692 drw 10

- 1. R/W or CE must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of \overline{CE} = VIL and R/ \overline{W} = VIL.
- 3. twn is measured from the earlier of $\overline{\text{CE}}$ or R/\overline{W} going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal (CE or R/W) is asserted last.
- 7. This parameter is determined be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If \overrightarrow{OE} is LOW during a R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tbw) to allow the I/O drivers to turn off data to be placed on the bus for the required tbw. If \overrightarrow{OE} is HIGH during a R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(7,8)

		7132X20 ⁽¹⁾ 7142X20 ⁽¹⁾ Com'l Only		7132X25 ⁽²⁾ 7142X25 ⁽²⁾ Com'l, Ind & Military		7132X35 7142X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY Timing	(For Master IDT7132 Only)							
t BAA	BUSY Access Time from Address		20		20		20	ns
tbda	BUSY Disable Time from Address		20	_	20		20	ns
t BAC	BUSY Access Time from Chip Enable		20		20		20	ns
tBDC	BUSY Disable Time from Chip Enable		20	_	20	_	20	ns
twdd	Write Pulse to Data Delay ⁽²⁾		50	_	50	-	60	ns
twn	Write Hold After BUSY ⁽⁶⁾	12	_	15	_	20		ns
todo	Write Data Valid to Read Data Delay ⁽²⁾		35	_	35	-	35	ns
taps	Arbitration Priority Set-up Time ⁽³⁾	5		5	-	5		ns
tBDD	BUSY Disable to Valid Data ⁽⁴⁾	_	25	_	35	_	35	ns
BUSY Timing (For Slave IDT7142 Only)								
twB	Write to BUSY Input ⁽⁵⁾	0		0	_	0		ns
twn	Write Hold After BUSY ⁽⁶⁾	12	_	15		20	_	ns
twdd	Write Pulse to Data Delay ⁽²⁾		40		50	_	60	ns
todo	Write Data Valid to Read Data Delay ⁽²⁾	_ 30 _ 35 _			35	ns		

2692 tbl 11a

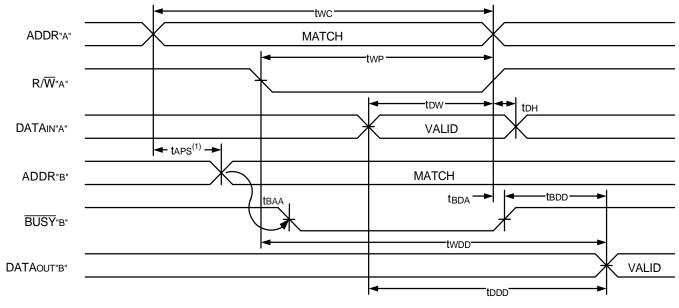
	7132X55 7142X55 Com'l & Military				7132X100 7142X100 Com'l & Military	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
BUSY Timing	(For Master IDT7132 Only)					
tbaa	BUSY Access Time from Address		30		50	ns
tbda	BUSY Disable Time from Address	_	30	_	50	ns
tBAC	BUSY Access Time from Chip Enable	_	30	_	50	ns
tBDC	BUSY Disable Time from Chip Enable	_	30	_	50	ns
twdd	Write Pulse to Data Delay ⁽²⁾	_	80	_	120	ns
twн	Write Hold After BUSY ⁽⁶⁾	20	-	20	_	ns
todd	Write Data Valid to Read Data Delay ⁽²⁾	_	55	_	100	ns
taps	Arbitration Priority Set-up Time ⁽³⁾	5	_	5	_	ns
tBDD	BUSY Disable to Valid Data ⁽⁴⁾		50		65	ns
BUSY Timing	(For Slave IDT7142 Only)					
twB	Write to BUSY Input ⁽⁵⁾	0		0	_	ns
twн	Write Hold After BUSY ⁽⁶⁾	20	_	20	_	ns
twdd	Write Pulse to Data Delay ⁽²⁾		80	_	120	ns
todd	Write Data Valid to Read Data Delay ⁽²⁾		55		100	ns

NOTES:

2692 tbl 11b

- 1. PLCC package only.
- 2. Port-to-port delay through RAM cells from the writing port to the reading port, refer to "Timing Waveform of Write with Port -to-Port Read and BUSY."
- 3. To ensure that the earlier of the two ports wins.
- 4. tbdd is a calculated parameter and is the greater of 0, twdd twp (actual) or tddd tdw (actual).
- 5. To ensure that a write cycle is inhibited on port "B" during contention on port "A".
- 6. To ensure that a write cycle is completed on port "B" after contention on port "A".
- 7. 'X' in part numbers indicates power rating (SA or LA).
- 8. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Timing Waveform of Write with Port-to-Port Read and **BUSY**(2,3,4)

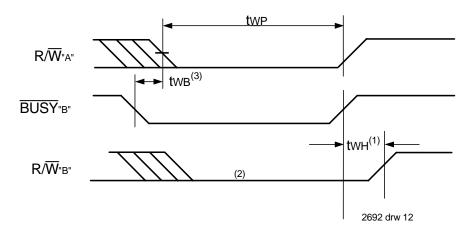


NOTES:

2692 drw 11

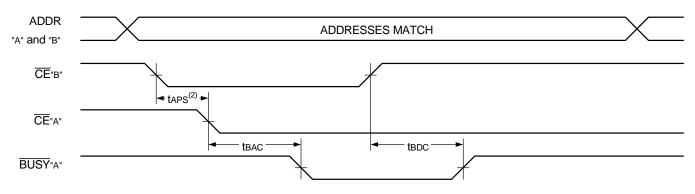
- 1. To ensure that the earlier of the two ports wins. taps is ignored for Slave (IDT7142).
- 2. $\overline{CE}L = \overline{CE}R = VIL$
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of Write with **BUSY**(4)



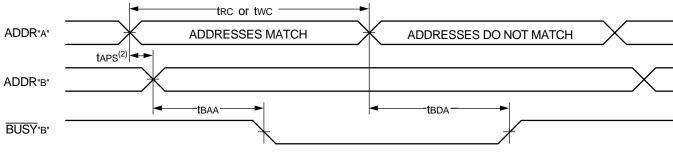
- 1. twn must be met for both BUSY Input (IDT7142, slave) or Output (IDT7132, master).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. twb applies only to the slave version (IDT7142).
- 4. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of **BUSY** Arbitration Controlled by **CE** Timing⁽¹⁾



2692 drw 13

Timing Waveform of **BUSY** Arbitration Controlled by Address Match Timing⁽¹⁾



2692 drw 14

NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. If taps is not satisified, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted (7132 only).

Truth Tables

Table I. Non-Contention Read/Write Control⁽⁴⁾

Left or Right Port ⁽¹⁾				
R/W	ΖĒ	ŌĒ	D0-7	Function
Х	Н	Х	Z	Port Disabled and in Power-Down Mode, ISB2 or ISB4
Х	Н	Х	Z	$\overline{CER} = \overline{CEL} = VIH$, Power-Down Mode, ISB1 or ISB3
L	L	Χ	DATAIN	Data on Port Written into Memory ⁽²⁾
Н	L	L	DATAOUT	Data in Memory Output on Port ⁽³⁾
Х	L	Н	Z	High Impedance Outputs

2692 tbl 12

- 1. AOL A10L \neq AOR A10R
- 2. If BUSY = L, data is not written.
- 3. If BUSY = L, data may not be valid, see twop and topp timing.
- 4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

Table II — Address **BUSY** Arbitration

Inputs			Out	puts	
ΕĒL	CER	AOL-A10L AOR-A10R	BUSYL ⁽¹⁾ BUSYR ⁽¹⁾		Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Χ	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

1. Pins BUSYL and BUSYR are both outputs for IDT7132 (master). Both are inputs for IDT7142 (slave). BUSYx outputs on the IDT7132 are open drain, not push-pull outputs. On slaves the BUSYx input internally inhibits writes.

2692 tbl 13

- 2. 'L'if the inputs to the opposite port were stable prior to the address and enable inputs of this port. 'H' if the inputs to the opposite port became stable after the address and enable inputs of this port. If taps is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.
- 3. Writes to the left port are internally ignored when $\overline{\text{BUSY}}\text{L}$ outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Functional Description

The IDT7132/IDT7142 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7132/IDT7142 has an automatic power down feature controlled by \overline{CE} . The \overline{CE} controls onchip power down circuitry that permits the respective port to go into a standby mode when not selected (\overline{CE} = VIH). When a port is enabled, access to the entire memory array is permitted.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a busy indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY Logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation.

The BUSY outputs on the IDT7132 RAM master are open drain type outputs and require open drain resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array does not require the use of an external AND gate.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an SRAM array in width while using BUSY logic, one master part is used to decide which side of the SRAM array will receive a BUSY indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the BUSY signal as a write inhibit signal. Thus on the IDT7132/ IDT7142 SRAMs the BUSY pin is an output if the part is Master (IDT7132), and the BUSY pin is an input if the part is a Slave (IDT7142) as shown in Figure 3.

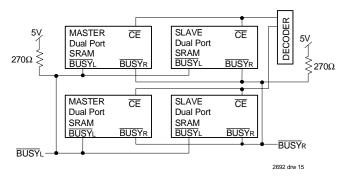
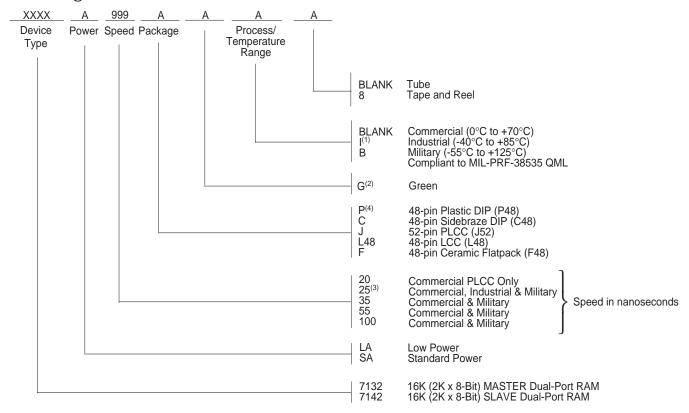


Figure 4. Busy and chip enable routing for both width and depth expansion with IDT7132 (Master) and (Slave) IDT7142 SRAMs.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the array and another master indicating BUSY on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a Master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write pulse can be initiated with either the R/W signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Ordering Information



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NOTES:

- 1. Industrial temperature range is available. For specific speeds, packages and powers contact your sales office.
- Green parts available. For specific speeds, packages and powers contact your local sales office. LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice - PDN# SP-17-02
- 3. 25ns speed grade not available in DIP packages.
- 4. For "P", Plastic DIP, when ordering green package, the suffix is "PDG".

Datasheet Document History

03/24/99:		Initiated datasheet document history
		Converted to new format
		Cosmetic and typographical corrections
	Pages 2 and 3	Added additional notes to pin configurations
06/08/99:		Changed drawing format Changed drawing for Changed drawing format Changed drawing for Ch
08/26/99:	Page 14	Changed Busy Logic and Width Expansion copy
11/10/99:		Replaced IDT logo
01/12/00:	Pages 1 and 2	Moved full "Description" to page 2 and adjusted page layouts
	Page 1	Added "(LAonly)" to paragraph
	Page 2	Fixed P48-1 body package description
	Page 3	Increased storage temperature parameters
		Clarified TA parameter
	Page 4	DC Electrical parameters-changed wording from "open" to "disabled"
	Page 6	Added asteriks to Figures 1 and 3 in drw 06
	Page 14	Corrected part numbers
		Changed ±500mV to 0mV in notes
		Datasheet Document History continued on page 16

Datasheet Document History (cont'd)

06/11/04:	Page 6 Page 4, 7, 9,	Corrected errors in Figure 3 by changing 1250Ω to 270Ω and removing "or Int" and Int Clarified Industrial temp offering for 25ns
	11 & 15	
	Page 5	Removed INT from Vol parameter in DC Electrical Characteristics table
	Page 6	Updated AC Test Conditions Input Rise/Fall Times from 5ns to 3ns
01/17/06:	Page 1	Added green availability to features
	Page 15	Added green indicator to ordering information
	Page 16	Replaced IDT address with new
10/21/08:	Page 15	Removed "IDT" from orderable part number
09/20/10:	Page 14	Corrected BUSY description to indicate open drain outputs
10/03/14:	Page 2	Removed IDT in reference to fabrication
	Page 15	Added Tape and Reel to Ordering Information
	Page 2, 3 & 15	The package codes P48-1, C48-2, J52-1, L48-1 & F48-1 changed to P48, C48, J52, L48 & F48 respectively to match standard package codes
	Page 15	Add annotation (3) to 25ns speed grade to indicate that 25ns is not available in DIP
	rage 15	packages
10/08/14:	Page 15	Corrected a typo
11/20/15:	Page 15	Added (4) footnote annotation to the "P" package in the Ordering Information. Added footnote 4, For "P", Plastic DIP, when ordering green package, the suffix is "PDG".
07/03/18:		Updated L package in the Ordering Information to L48 Product Discontinuation Notice - PDN# SP-17-02 Last time buy expires June 15, 2018

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